



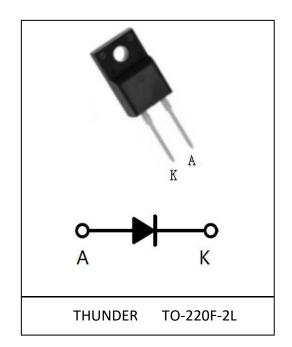
Thunder High Power Products

FRED Ultrafast Soft Recovery Diode, 15A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction

Product Summary	
Vr	600 V
IF(AV)	15A
trr	24 ns



Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings

Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	Vrrm		600	V
Continuous forward current	lf(AV)	Tc =110°C	15	
Single pulse forward current	IFSM	Tc =25°C	150	А
Maximum repetitive forward current	IFRM	Square wave, 20kHZ	30	
Operating junction	Тј		175	°C
Storage temperatures	Tstg		-55 to +175	°C

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Electrical characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units
Breakdown voltage Blocking voltage	VBR, V _R	Ir=100µA	600	_	_	
Forward voltage	VF	IF=15A	_	1.35	1.70	V
		I _F =15A, Tj =125°C	_	1.25	1.60	
Reverse leakage	İR	Vr= Vrrm	_	_	20	μΑ
current		Tj=150°C, Vr=600V	_	_	200	
Reverse recovery		I _F =0.5A, I _R =1A, I _{RR} =0.25A	_	35	50	ns
time	trr	I _F =1A,V _R =30V, di/ <i>dt</i> =200A/us	_	24	35	
Reverse recovery time	trr	$I_F=15A, V_R=300V,$ $di/dt=-200A/us,$ $T_i=25^{\circ}C$	_	48	_	ns
		$I_F=15A, V_R=300V,$ $di/dt=-200A/us,$ $T_j=125^{\circ}C$	_	84	_	ns
Reverse Recovery Charge	$I_F=15A, V_R=300V,$ $di/dt=-200A/us,$ $T_j=25^{\circ}C$	_	130	_	nC	
	Qrr	I_F =15A, V_R =300V, di/ dt =-200A/us, T_j =125 $^{\circ}$ C	_	470	_	nC
Peak Reverse Recovery Current		I_F =15A, V_R =300V, di/ dt =-200A/us, T_j =25 $^{\circ}$ C	_	4.0	_	А
	IRM	I_F =15A, V_R =300V, di/ dt =-200A/us, T_j =125 $^{\circ}$ C	_	7.0	_	Α

Thermal characteristics

Paramter	Symbol	Тур	Units
Junction-to-Case	$R_{ heta IC}$	2.5	°C/W

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Electrical performance (typical)

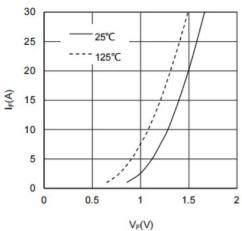


Figure 1. Forward Voltage Drop vs Forward Current

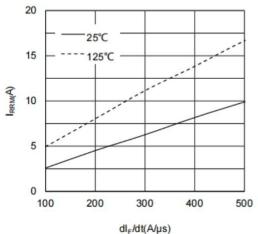


Figure 3. Reverse Recovery Current vs dl_F/dt

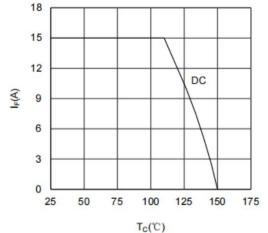


Figure 5. Forward current vs Case temperature

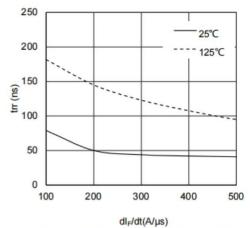


Figure 2. Reverse Recovery Time vs dl_F/dt

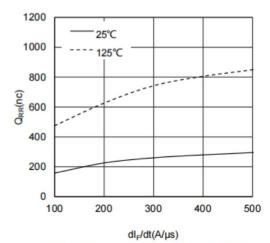
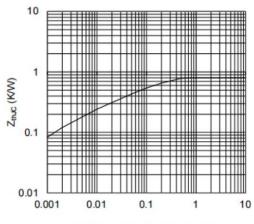


Figure 4. Reverse Recovery Charge vs dl_F/dt



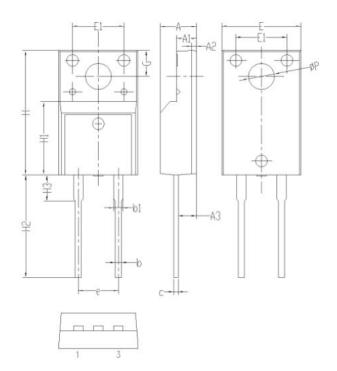
Rectangular Pulse Duration (s)
Figure 6.Transient Thermal Impedance

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Package Information

TO-220F-2L PACKAGE



Cumbal	Dimensions(millimeters)		
Symbol	Min.	Max.	
А	4.35	4.75	
A1	2.30	2.70	
A2	0.40	0.80	
A3	2.10	2.50	
b	0.60	1.00	
b1	1.00	1.40	
С	0.30	0.70	
е	4.60	5.40	
Е	9.80	10.2	
E1	6.30	6.70	
Н	15.6	16.0	
H1	8.80	9.20	
H2	12.9	13.5	
H3	3.10	3.50	
G	3.10	3.50	
ΦР	3.10	3.50	

Notice

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